LM386 低電圧オーディオ・パワー・アンプ

1 特長

- バッテリでの動作
- 必要な外付け部品が最小限
- 広い電源電圧範囲: 4V～12Vまたは5V～18V
- 低い静止消費電流: 4mA
- 20～200の電圧ゲイン
- 入力はグランドが基準
- 出力静止電圧の自己センタリング
- 低歪: 0.2% (A_V = 20、V_S = 6V、R_L = 8Ω、P_O = 125mW、f = 1kHz)
- 8ピンのMSOPパッケージで供給

2 アプリケーション

- AM/FMラジオのアンプ
- 携帯テープ・プレーヤのアンプ
- インターコム
- テレビ用サウンド・システム
- ライン・ドライバ
- 超音波ドライバ
- 小型サーボ・ドライバ
- パワー・コンバータ

3 概要

LM386M-1およびLM386MX-1は、低電圧の消費者向けアプリケーションで使用するよう設計されたパワー・アンプです。外付け部品数を減らすため、ゲインは内部的に20に設定されていますが、ピン1と8との間に外付け抵抗とコンデンサを追加すると、20～200の任意の値にゲインを増大できます。

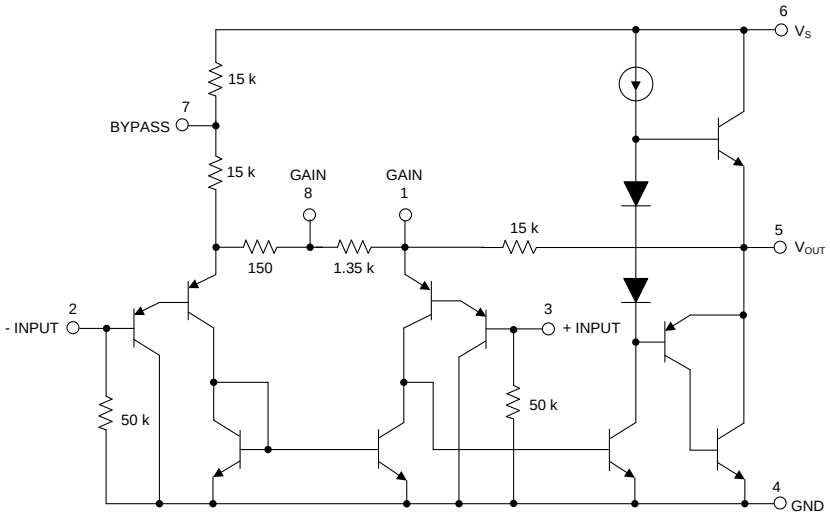
入力はグランドを基準とし、出力は自動的に電源電圧の半分にバイアスされます。静止時の消費電力は6V電源での動作時にわずか24mWであるため、LM386M-1およびLM386MX-1はバッテリでの動作に最適です。

製品情報(1)

型番	パッケージ	本体サイズ(公称)
LM386N-1	PDIP (8)	9.60mm×6.35mm
LM386N-3	PDIP (8)	9.60mm×6.35mm
LM386N-4	PDIP (8)	9.60mm×6.35mm
LM386M-1	SOIC (8)	4.90mm×3.90mm
LM386MX-1	SOIC (8)	4.90mm×3.90mm
LM386MMX-1	VSSOP (8)	3.00mm×3.00mm

(1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。

回路図



目次

4 改訂履歴

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Revision B (March 2017) から **Revision C** に変更 **Page**

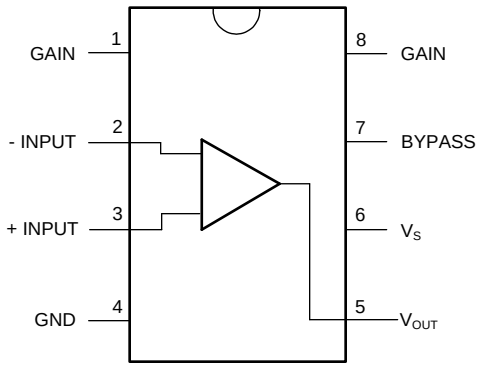
- データシートのタイトルでデバイスをLM386M-1/LM386MX-1からLM386に変更 ... 1
- Changed From: LM386N-4 To: Speaker Impedance in the *Recommended Operating Conditions* table ... 4
- Changed From: 5 Ω to 12 Ω To: 5 V to 12 V for Supply Voltage in Table 1 ... 8
- Changed kW To: kΩ in the *Gain Control* section ... 8
- Changed kW To: kΩ in the *Input Biasing* section ... 9
- Changed Figure 11 ... 9
- Changed From: 5 Ω to 12 Ω To: 5 V to 12 V for Supply Voltage in Table 2 ... 10
- Changed Figure 13 ... 10
- Changed From: 5 Ω to 12 Ω To: 5 V to 12 V for Supply Voltage in Table 3 ... 11
- Changed Figure 15 ... 11
- Changed From: 5 Ω to 12 Ω To: 5 V to 12 V for Supply Voltage in Table 4 ... 12
- Changed Figure 17 ... 12
- Changed From: 5 Ω to 12 Ω To: 5 V to 12 V for Supply Voltage in Table 5 ... 13
- Changed From: 5 Ω to 12 Ω To: 5 V to 12 V for Supply Voltage in Table 6 ... 14
- Changed Figure 21 ... 14
- Changed From: 5 Ω to 12 Ω To: 5 V to 12 V for Supply Voltage in Table 7 ... 15
- Changed Figure 23 ... 15

Revision A (May 2004) から **Revision B** に変更 **Page**

- LM386MX-1デバイスをデータシートに 追加 ... 1
- 「製品情報」、「アプリケーションと実装」、「電源に関する推奨事項」、「レイアウト」、「デバイスおよびドキュメントのサポート」の各セクションを追加 ... 1
- Inserted Functional Block Diagram ... 7

5 Pin Configuration and Functions

D Package
8-Pin MSOP
Top View



Pin Functions

PIN		TYPE	DESCRIPTION
NAME	NO.		
GAIN	1	–	Gain setting pin
–INPUT	2	I	Inverting input
+INPUT	3	I	Noninverting input
GND	4	P	Ground reference
V_{OUT}	5	O	Output
V_S	6	P	Power supply voltage
BYPASS	7	O	Bypass decoupling path
GAIN	8	–	Gain setting pin

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
Supply Voltage, V_{CC}	LM386N-1/-3, LM386M-1		15	V
	LM386N-4		22	
Package Dissipation	LM386N		1.25	W
	LM386M		0.73	
	LM386MM-1		0.595	
Input Voltage, V_I		–0.4	0.4	V
Storage temperature, T_{stg}		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$ Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±1000	V
	Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	±1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{CC}	Supply Voltage	4		12	V
	LM386N-4	5		18	V
	Speaker Impedance	4			Ω
VI	Analog input voltage	–0.4		0.4	V
TA	Operating free-air temperature	0		70	°C

6.4 Thermal Information

THERMAL METRIC(1)		LM386 D (SOIC) 8	LM386 DGK (VSSOP) 8	LM386 P (PDIP) 8	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	115.7	169.3	53.4	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	59.7	73.1	42.1	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	56.2	100.2	30.6	°C/W
ψ_{JT}	Junction-to-top characterization parameter	12.4	9.2	19.0	°C/W
ψ_{JB}	Junction-to-board characterization parameter	55.6	99.1	50.5	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

6.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_S	Operating Supply Voltage	LM386N-1, -3, LM386M-1, LM386MM-1	4		12	V
		LM386N-4	5		18	
I_Q	Quiescent Current	V_S = 6 V, V_{IN} = 0		4	8	mA
P_{OUT}	Output Power	V_S = 6 V, R_L = 8 Ω, THD = 10% (LM386N-1, LM386M-1, LM386MM-1)	250	325		mW
		V_S = 9 V, R_L = 8 Ω, THD = 10% (LM386N-3)	500	700		
		V_S = 16 V, R_L = 32 Ω, THD = 10% (LM386N-4)	700	100		
A_V	Voltage Gain	V_S = 6 V, f = 1 kHz		26		dB
		10 µF from Pin 1 to 8		46		
BW	Bandwidth	V_S = 6 V, Pins 1 and 8 Open		300		kHz
THD	Total Harmonic Distortion	V_S = 6 V, R_L = 8 Ω, POUT = 125 mW f = 1 kHz, Pins 1 and 8 Open		0.2%		
PSRR	Power Supply Rejection Ratio	V_S = 6 V, f = 1 kHz, CBYPASS = 10 µF Pins 1 and 8 Open, Referred to Output		50		dB
R_{IN}	Input Resistance			50		kΩ
I_{BIAS}	Input Bias Current	V_S = 6 V, Pins 2 and 3 Open		250		nA

6.6 Typical Characteristics

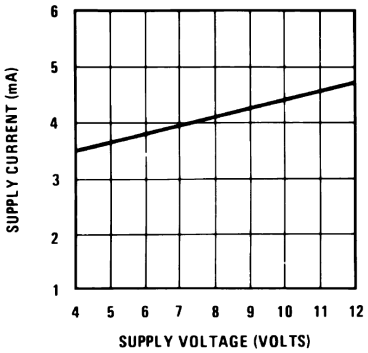


Figure 1. Supply Current vs Supply Voltage

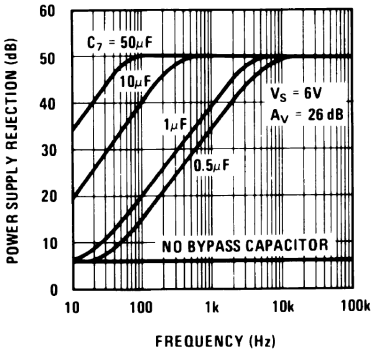


Figure 2. Power Supply Rejection vs Frequency

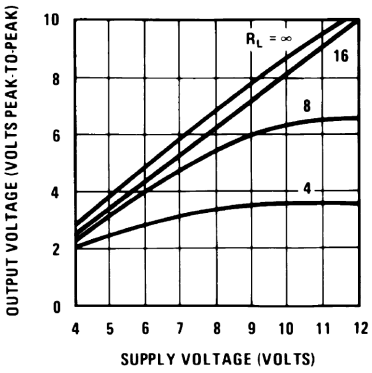


Figure 3. Output Voltage vs Supply Voltage

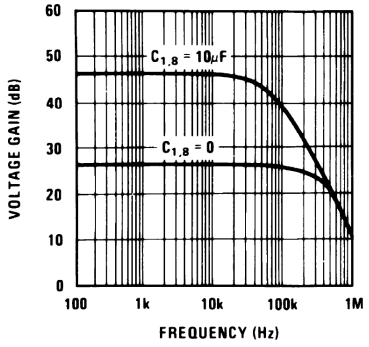


Figure 4. Voltage Gain vs Frequency

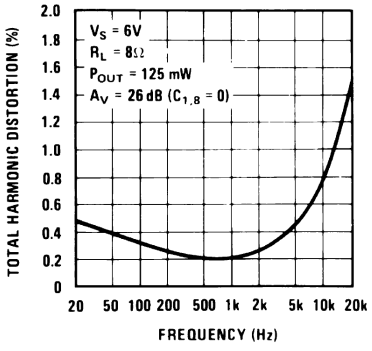


Figure 5. Total Harmonic Distortion vs Frequency

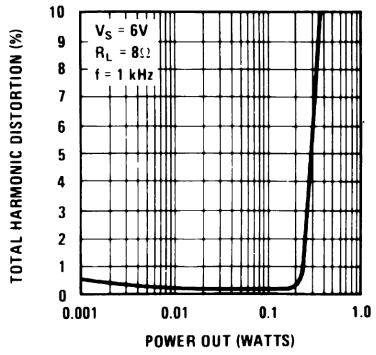


Figure 6. Total Harmonic Distortion vs Power Out

Typical Characteristics (continued)

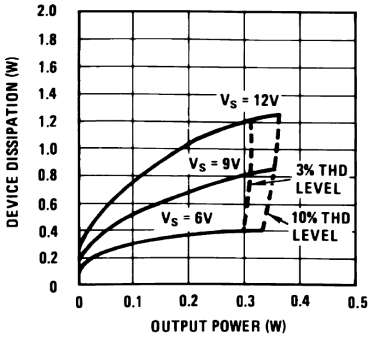


Figure 7. Device Dissipation vs Output Power

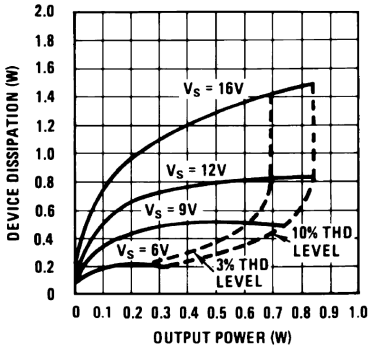


Figure 8. Device Dissipation vs Output Power

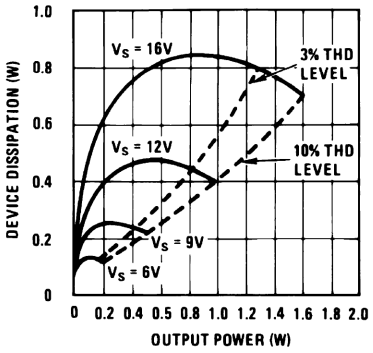


Figure 9. Device Dissipation vs Output Power

7 Parameter Measurement Information

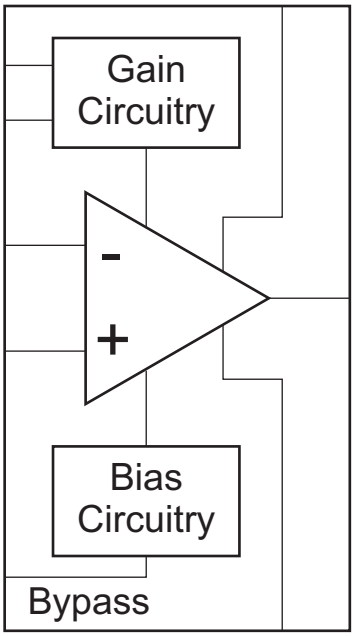
All parameters are measured according to the conditions described in the *Specifications* section.

8 Detailed Description

8.1 Overview

The LM386 is a mono low voltage amplifier that can be used in a variety of applications. It can drive loads from 4 Ω to 32 Ω. The gain is internally set to 20 but it can be modified from 20 to 200 by placing a resistor and capacitor between pins 1 and 8. This device comes in three different 8-pin packages as PDIP, SOIC and VSSOP to fit in different applications.

8.2 Functional Block Diagram



8.3 Feature Description

There is an internal 1.35-KΩ resistor that sets the gain of this device to 20. The gain can be modified from 20 to 200. Detailed information about gain setting can be found in the *Detailed Design Procedure* section.

8.4 Device Functional Modes

As this is an Op Amp it can be used in different configurations to fit in several applications. The internal gain setting resistor allows the LM386 to be used in a very low part count system. In addition a series resistor can be placed between pins 1 and 5 to modify the gain and frequency response for specific applications.

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

Below are shown different setups that show how the LM386 can be implemented in a variety of applications.

9.2 Typical Application

9.2.1 LM386 with Gain = 20

Figure 10 shows the minimum part count application that can be implemented using LM386. Its gain is internally set to 20.

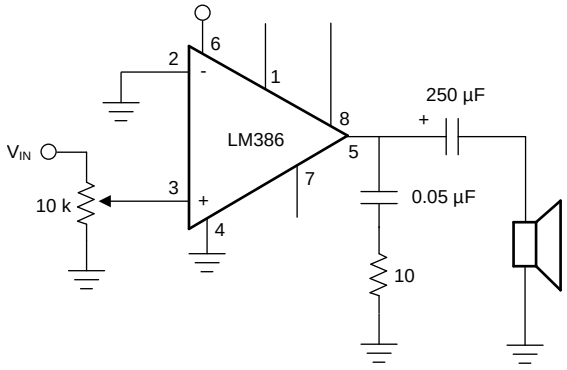


Figure 10. LM386 with Gain = 20

9.2.1.1 Design Requirements

Table 1. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
Load Impedance	4 Ω to 32 Ω
Supply Voltage	5 V to 12 V

9.2.1.2 Detailed Design Procedure

9.2.1.2.1 Gain Control

To make the LM386 a more versatile amplifier, two pins (1 and 8) are provided for gain control. With pins 1 and 8 open the 1.35-kΩ resistor sets the gain at 20 (26 dB). If a capacitor is put from pin 1 to 8, bypassing the 1.35-kΩ resistor, the gain will go up to 200 (46 dB). If a resistor is placed in series with the capacitor, the gain can be set to any value from 20 to 200. Gain control can also be done by capacitively coupling a resistor (or FET) from pin 1 to ground.

Additional external components can be placed in parallel with the internal feedback resistors to tailor the gain and frequency response for individual applications. For example, we can compensate poor speaker bass response by frequency shaping the feedback path. This is done with a series RC from pin 1 to 5 (paralleling the internal 15-kΩ resistor). For 6 dB effective bass boost: R ~= 15 kΩ, the lowest value for good stable operation is R = 10 kΩ if pin 8 is open. If pins 1 and 8 are bypassed then R as low as 2 kΩ can be used. This restriction is because the amplifier is only compensated for closed-loop gains greater than 9.

9.2.1.2.2 Input Biasing

The schematic shows that both inputs are biased to ground with a 50 kΩ resistor. The base current of the input transistors is about 250 nA, so the inputs are at about 12.5 mV when left open. If the dc source resistance driving the LM386 is higher than 250 kΩ it will contribute very little additional offset (about 2.5 mV at the input, 50 mV at the output). If the dc source resistance is less than 10 kΩ, then shorting the unused input to ground will keep the offset low (about 2.5 mV at the input, 50 mV at the output). For dc source resistances between these values we can eliminate excess offset by putting a resistor from the unused input to ground, equal in value to the dc source resistance. Of course all offset problems are eliminated if the input is capacitively coupled.

When using the LM386 with higher gains (bypassing the 1.35 kΩ resistor between pins 1 and 8) it is necessary to bypass the unused input, preventing degradation of gain and possible instabilities. This is done with a 0.1 μF capacitor or a short to ground depending on the dc source resistance on the driven input.

9.2.1.3 Application Curve

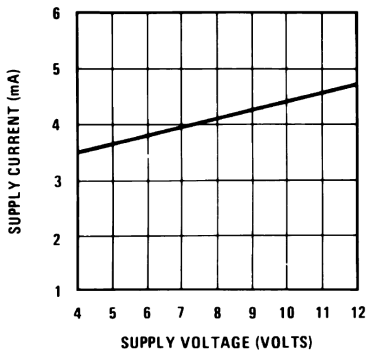


Figure 11. Supply Current vs Supply Voltage

9.2.2 LM386 with Gain = 200

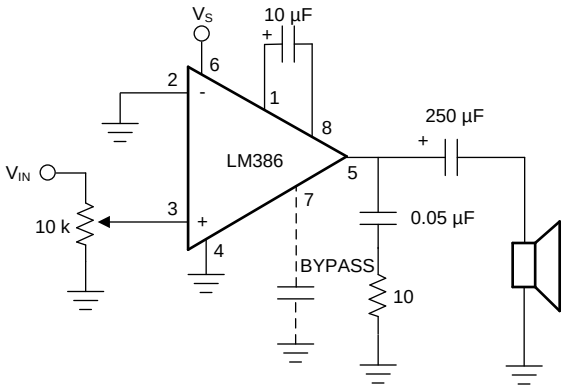


Figure 12. LM386 with Gain = 200

9.2.2.1 Design Requirements

Table 2. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
Load Impedance	4 Ω to 32 Ω
Supply Voltage	5 V to 12 V

9.2.2.2 Detailed Design Procedure

The Detailed Design Procedure can be found in the *Detailed Design Procedure* section.

9.2.2.3 Application Curve

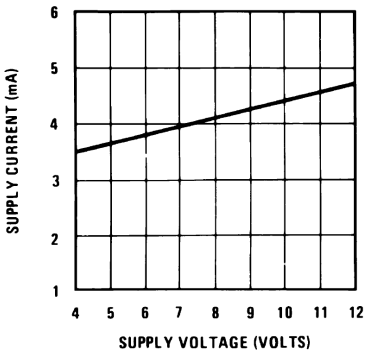


Figure 13. Supply Current vs Supply Voltage

9.2.3 LM386 with Gain = 50

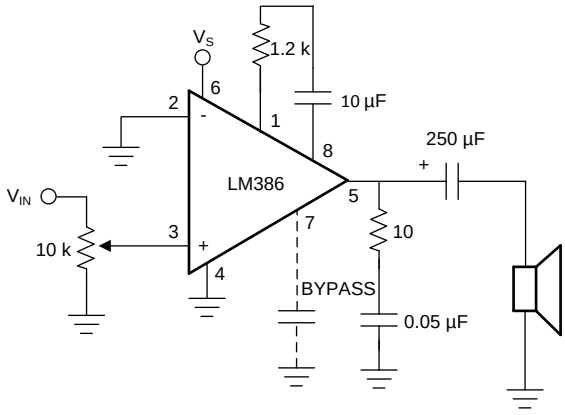


Figure 14. LM386 with Gain = 50

9.2.3.1 Design Requirements

Table 3. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
Load Impedance	4 Ω to 32 Ω
Supply Voltage	5 V to 12 V

9.2.3.2 Detailed Design Procedure

The Detailed Design Procedure can be found in the *Detailed Design Procedure* section.

9.2.3.3 Application Curve

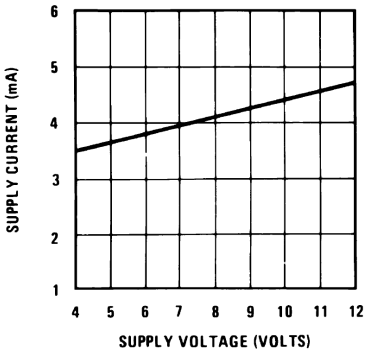


Figure 15. Supply Current vs Supply Voltage

9.2.4 Low Distortion Power Wienbridge Oscillator

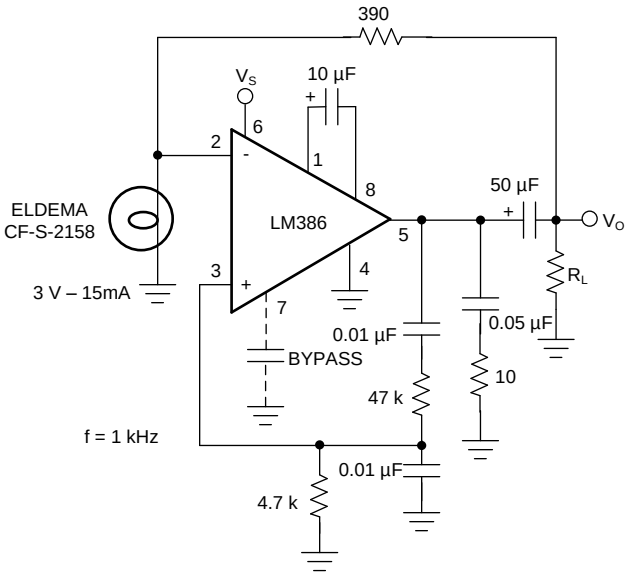


Figure 16. Low Distortion Power Wienbridge Oscillator

9.2.4.1 Design Requirements

Table 4. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
Load Impedance	4 Ω to 32 Ω
Supply Voltage	5 V to 12 V

9.2.4.2 Detailed Design Procedure

The Detailed Design Procedure can be found in the *Detailed Design Procedure* section.

9.2.4.3 Application Curve

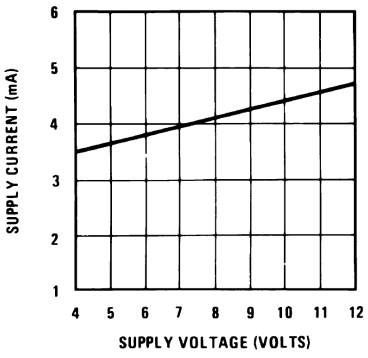


Figure 17. Supply Current vs Supply Voltage

9.2.5 LM386 with Bass Boost

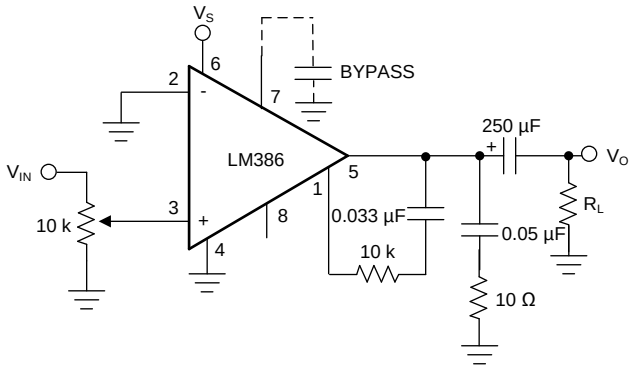


Figure 18. LM386 with Bass Boost

9.2.5.1 Design Requirements

Table 5. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
Load Impedance	4 Ω to 32 Ω
Supply Voltage	5 V to 12 V

9.2.5.2 Detailed Design Procedure

The Detailed Design Procedure can be found in the *Detailed Design Procedure* section.

9.2.5.3 Application Curve

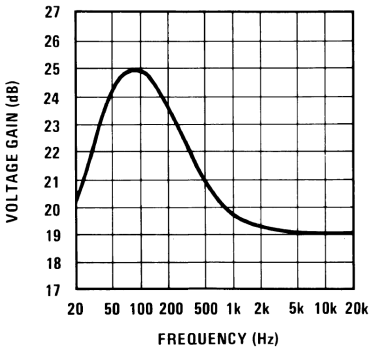


Figure 19. Voltage Gain vs Frequency

9.2.6 Square Wave Oscillator

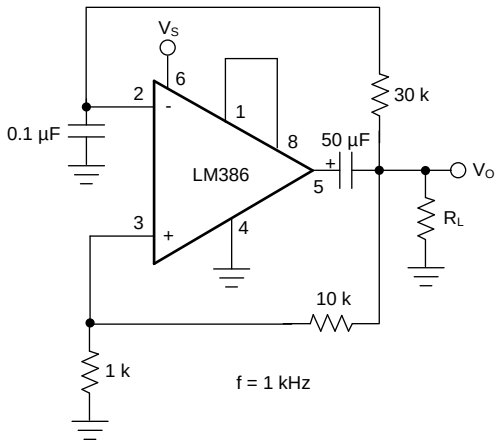


Figure 20. Square Wave Oscillator

Table 6. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
Load Impedance	4 Ω to 32 Ω
Supply Voltage	5 V to 12 V

9.2.6.1 Detailed Design Procedure

The Detailed Design Procedure can be found in the *Detailed Design Procedure* section.

9.2.6.2 Application Curve

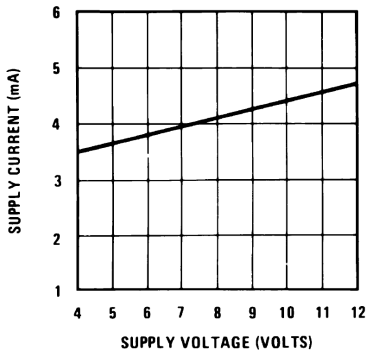


Figure 21. Supply Current vs Supply Voltage

9.2.7 AM Radio Power Amplifier

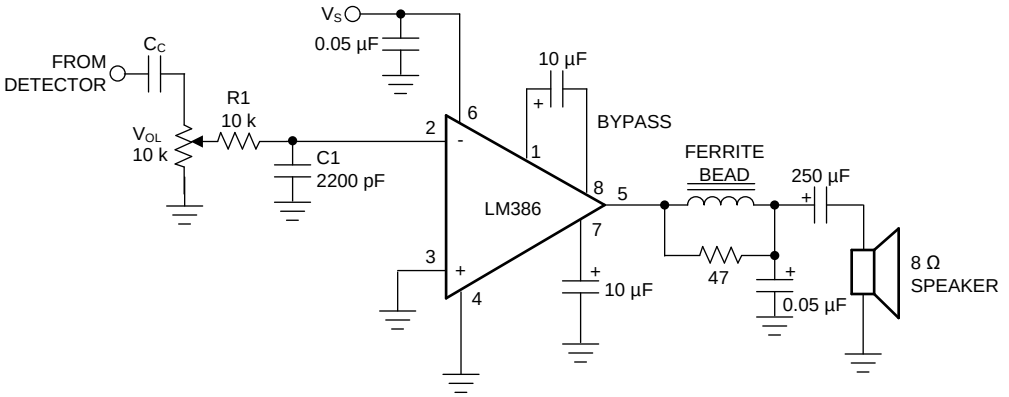


Figure 22. AM Radio Power Amplifier

9.2.7.1 Design Requirements

Table 7. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
Load Impedance	4 Ω to 32 Ω
Supply Voltage	5 V to 12 V

9.2.7.2 Detailed Design Procedure

The Detailed Design Procedure can be found in the *Detailed Design Procedure* section.

9.2.7.3 Application Curve

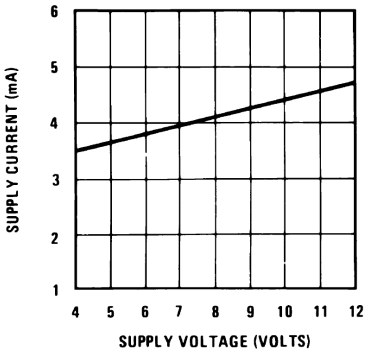


Figure 23. Supply Current vs Supply Voltage

10 Power Supply Recommendations

The LM386 is specified for operation up to 12 V or 18 V. The power supply should be well regulated and the voltage must be within the specified values. It is recommended to place a capacitor to GND close to the LM386 power supply pin.

11 Layout

11.1 Layout Guidelines

Place all required components as close as possible to the device. Use short traces for the output to the speaker connection. Route the analog traces far from the digital signal traces and avoid crossing them.

11.2 Layout Examples

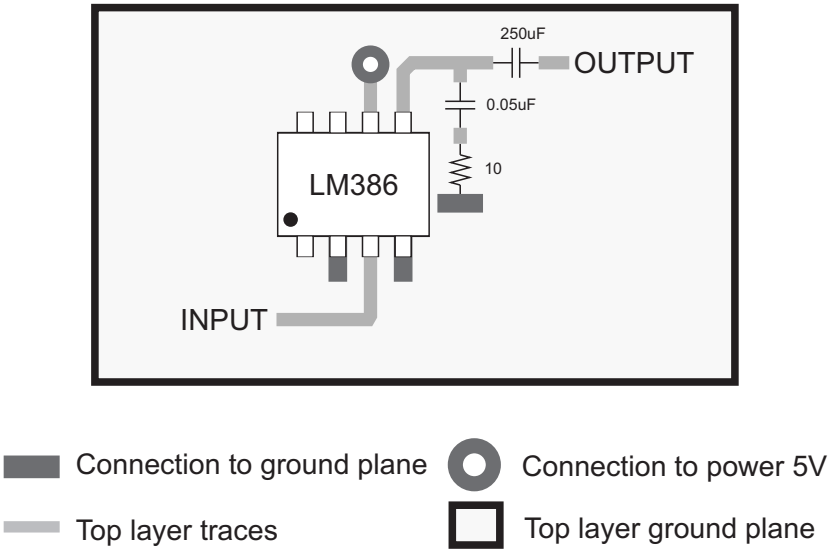


Figure 24. Layout Example for Minimum Parts Gain = 20 dB on PDIP package

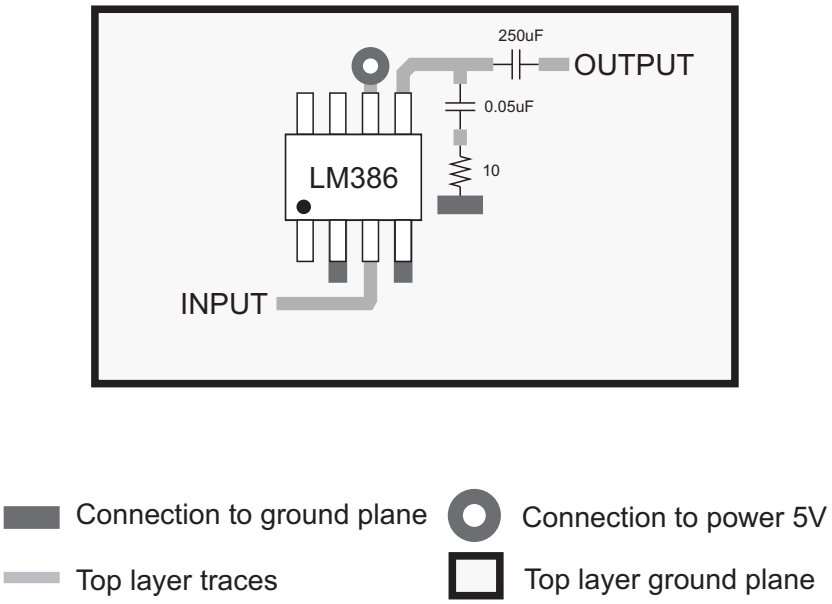


Figure 25. Layout Example for Minimum Parts Gain = 20 dB on SOIC package

Layout Examples (continued)

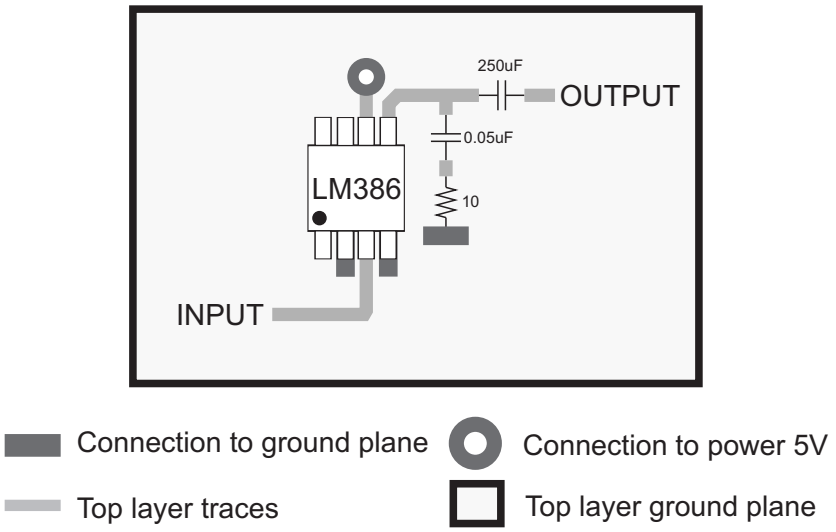


Figure 26. Layout Example for Minimum Parts Gain = 20 dB on VSSOP package

12 デバイスおよびドキュメントのサポート

12.1 デバイス・サポート

12.1.1 開発サポート

12.2 ドキュメントのサポート

12.3 関連リンク

次の表に、クイック・アクセス・リンクを示します。カテゴリには、技術資料、サポートおよびコミュニティ・リソース、ツールとソフトウェア、およびご注文へのクイック・アクセスが含まれます。

表 8. 関連リンク

製品	プロダクト・フォルダ	ご注文はこちら	技術資料	ツールとソフトウェア	サポートとコミュニティ
LM386M-1	ここをクリック	ここをクリック	ここをクリック	ここをクリック	ここをクリック
LM386MX-1	ここをクリック	ここをクリック	ここをクリック	ここをクリック	ここをクリック

12.4 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、ti.comで、お使いのデバイスの製品フォルダを開いてください。右上の隅にある「*通知を受け取る*」ボタンをクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

12.5 コミュニティ・リソース

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™オンライン・コミュニティ ***TIのE2E（Engineer-to-Engineer）コミュニティ。*** エンジニア間の共同作業を促進するために開設されたものです。e2e.ti.comでは、他のエンジニアに質問し、知識を共有し、アイディアを検討して、問題解決に役立てることができます。

設計サポート ***TIの設計サポート*** 役に立つE2Eフォーラムや、設計サポート・ ツールをすばやく見つけることができます。技術サポート用の連絡先情報も参照できます。

12.6 商標

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All other trademarks are the property of their respective owners.

12.7 静電気放電に関する注意事項

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12.8 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。この情報は、そのデバイスについて利用可能な最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LM386M-1/NOPB	ACTIVE	SOIC	D	8	95	Green (RoHS & no Sb/Br)	SN	Level-1-260C-UNLIM	0 to 70	LM386 M-1	Samples
LM386MMX-1/NOPB	ACTIVE	VSSOP	DGK	8	3500	Green (RoHS & no Sb/Br)	SN	Level-1-260C-UNLIM	0 to 70	Z86	Samples
LM386MX-1/NOPB	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	SN	Level-1-260C-UNLIM	0 to 70	LM386 M-1	Samples
LM386N-1/NOPB	ACTIVE	PDIP	P	8	40	Green (RoHS & no Sb/Br)	Call TI | SN	Level-1-NA-UNLIM	0 to 70	LM 386N-1	Samples
LM386N-3/NOPB	ACTIVE	PDIP	P	8	40	Green (RoHS & no Sb/Br)	SN	Level-1-NA-UNLIM	0 to 70	LM 386N-3	Samples
LM386N-4/NOPB	ACTIVE	PDIP	P	8	40	Green (RoHS & no Sb/Br)	Call TI | SN	Level-1-NA-UNLIM	0 to 70	LM 386N-4	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

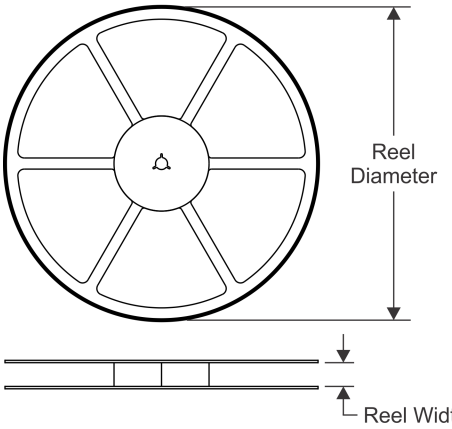
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

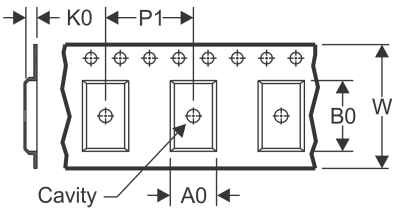
(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

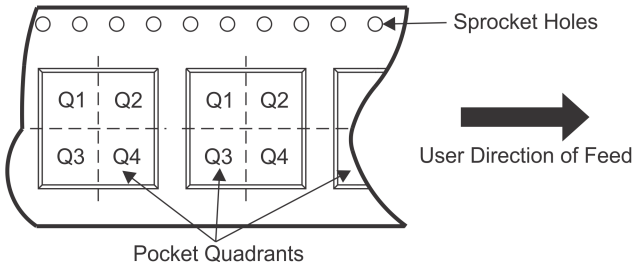


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

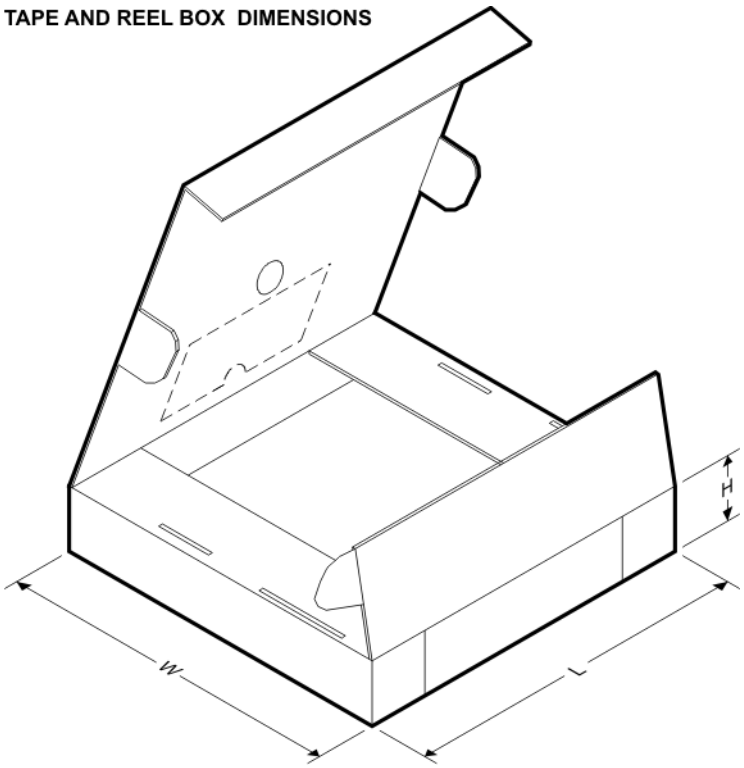
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

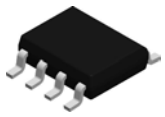
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LM386MMX-1/NOPB	VSSOP	DGK	8	3500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LM386MX-1/NOPB	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LM386MMX-1/NOPB	VSSOP	DGK	8	3500	367.0	367.0	35.0
LM386MX-1/NOPB	SOIC	D	8	2500	367.0	367.0	35.0

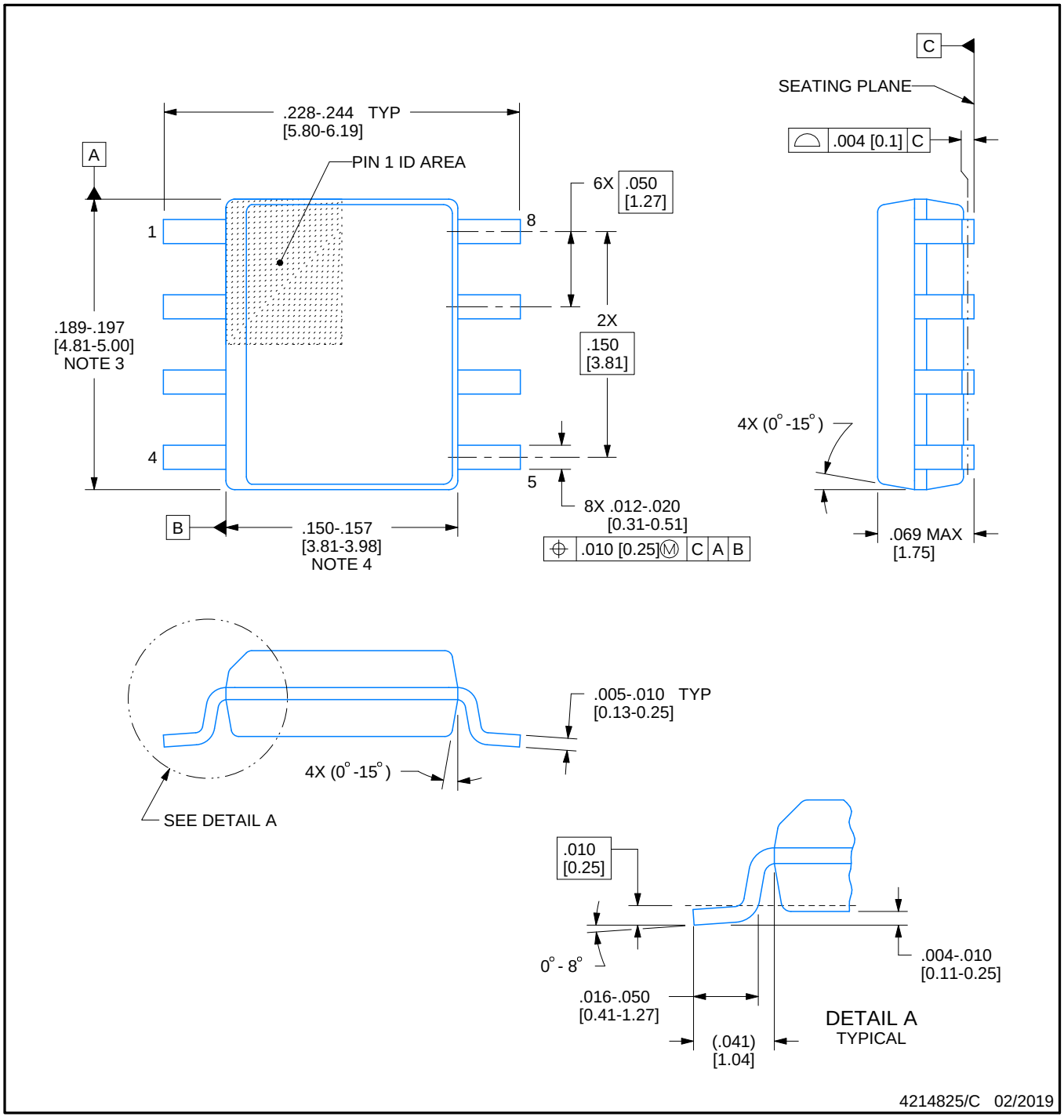


PACKAGE OUTLINE

D0008A

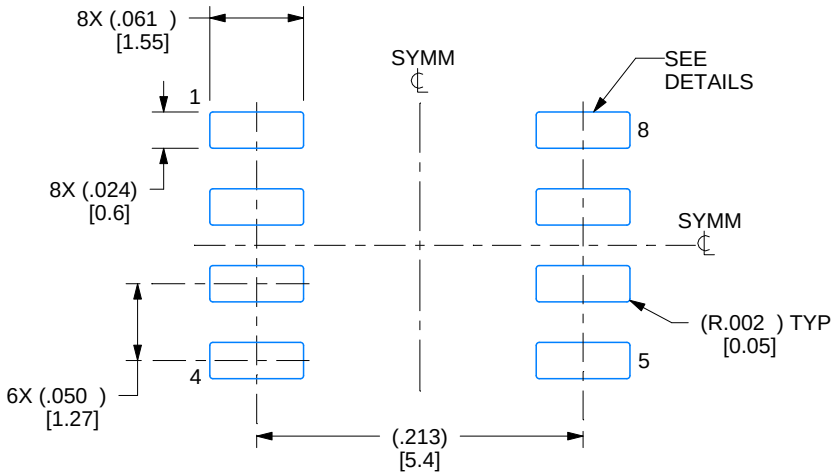
SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT

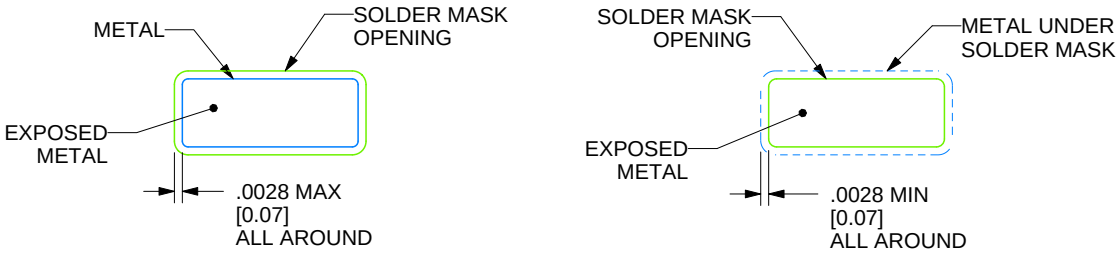


NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

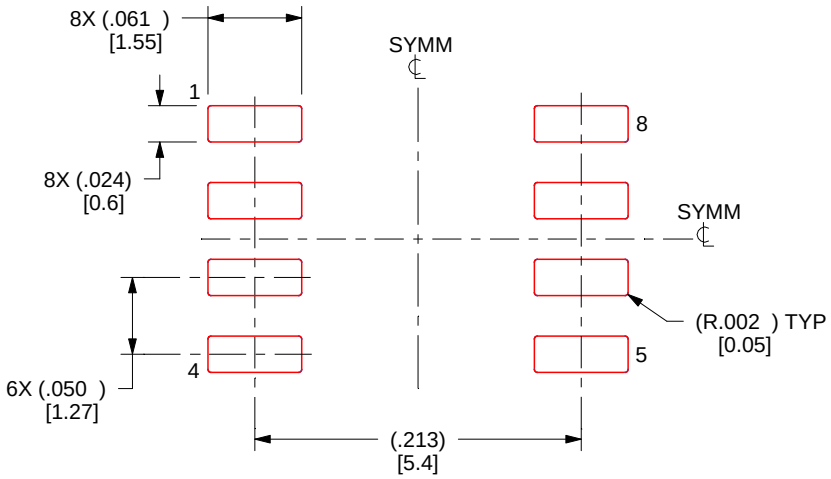
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



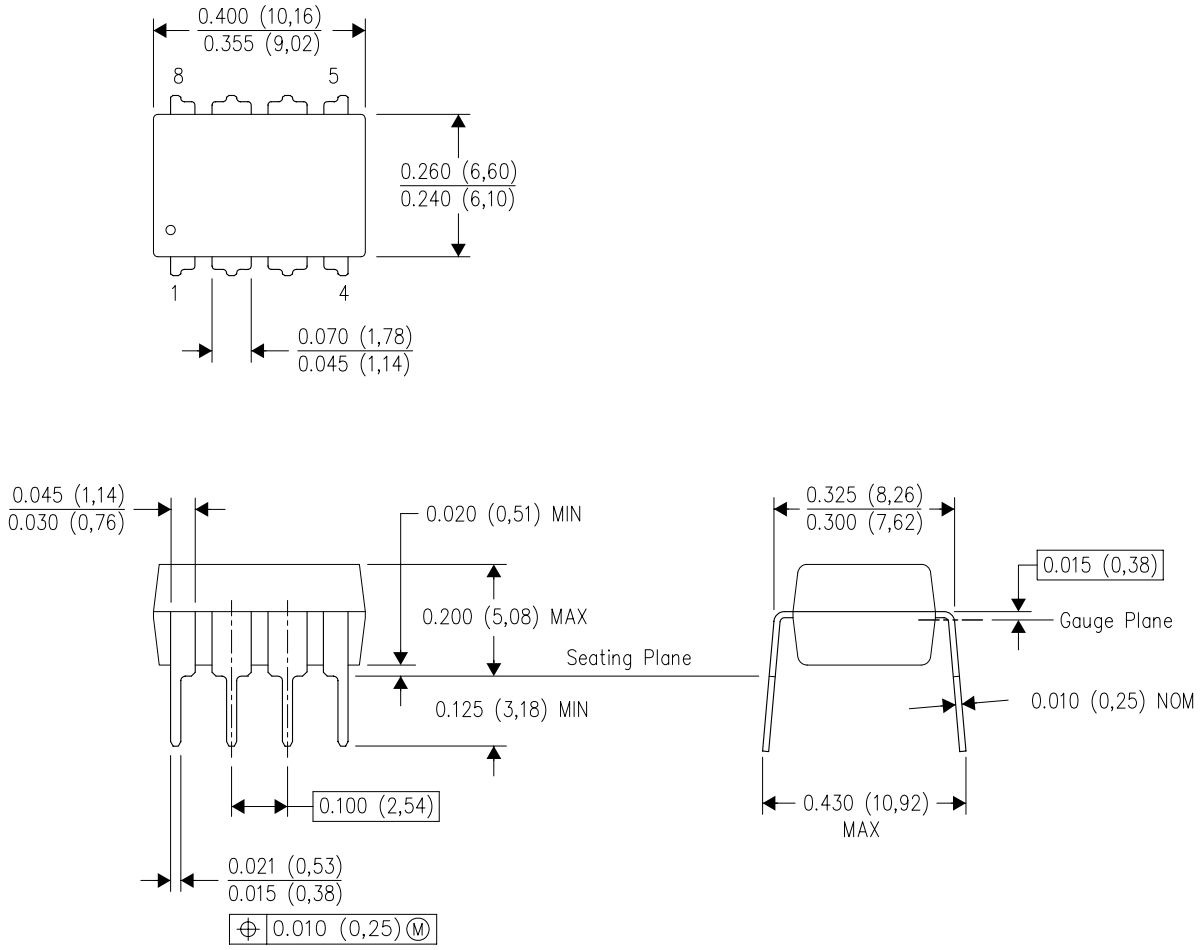
SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

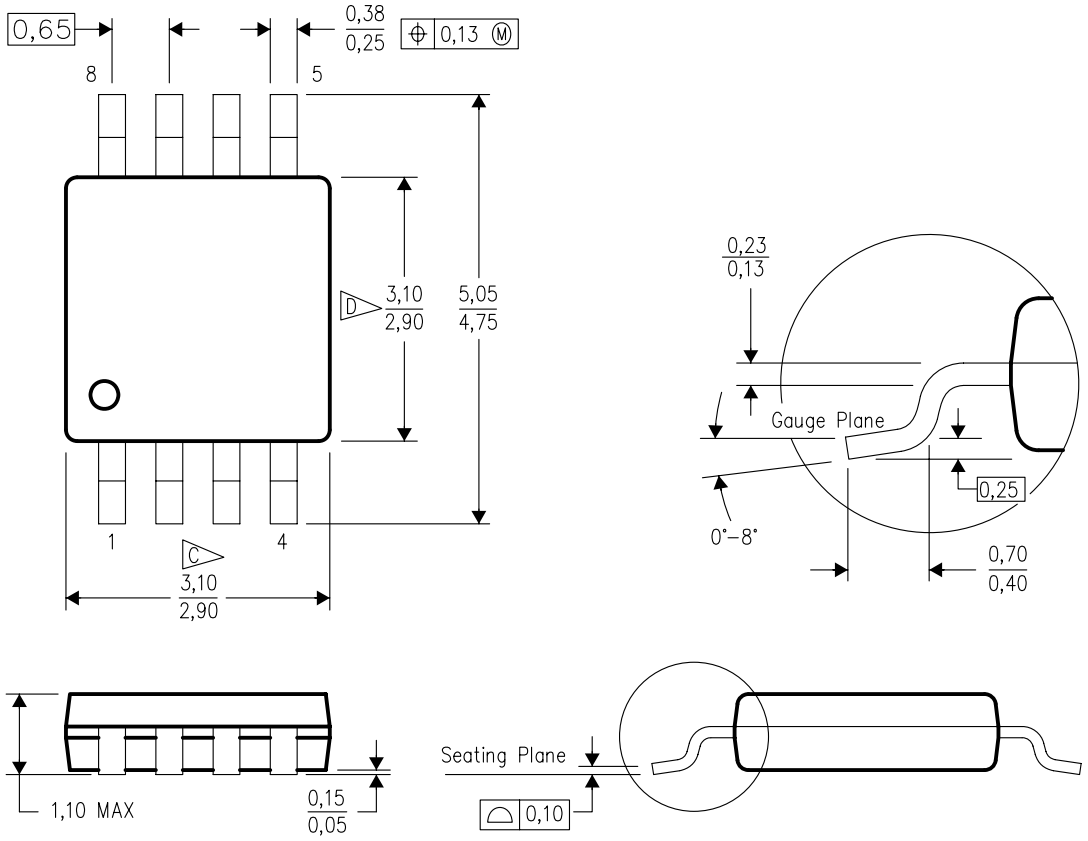
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

P (R–PDIP–T8) PLASTIC DUAL–IN–LINE PACKAGE



NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Falls within JEDEC MS–001 variation BA.

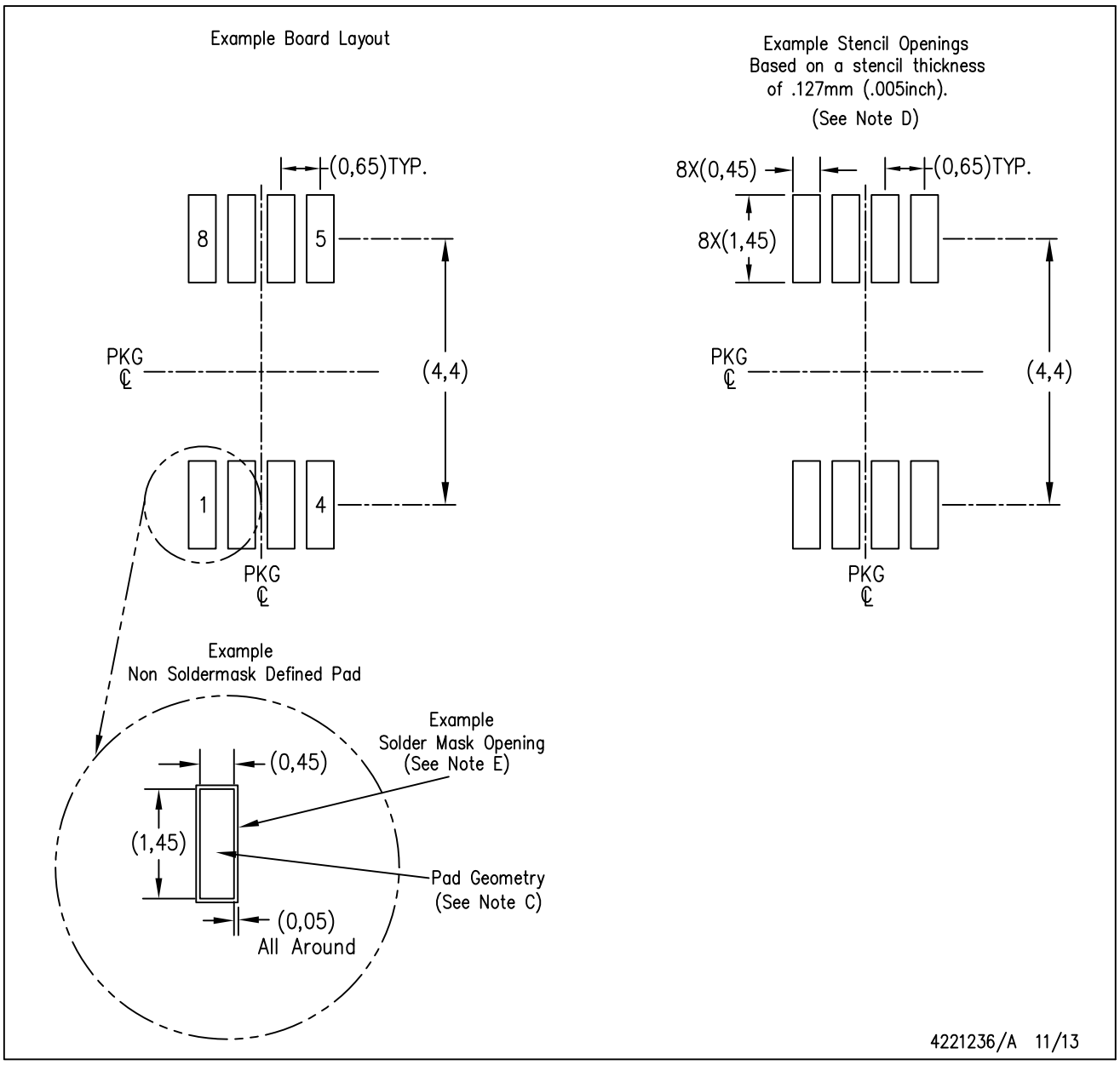
DGK (S–PDSO–G8) PLASTIC SMALL–OUTLINE PACKAGE



4073329/E 05/06

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per end.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
E. Falls within JEDEC MO–187 variation AA, except interlead flash.

DGK (S–PDSO–G8) PLASTIC SMALL OUTLINE PACKAGE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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